







DUAL 50V NPN SILICON LOW SATURATION SWITCHING TRANSISTOR

Features

- BV_{CEO} = 50V
- R_{SAT} = 160mV
- I_C = 1A Continuous Collector Current
- Low Equivalent On Resistance
- Low Saturation Voltage
- SOT23-6 package
- Lead, Halogen and Antimony Free, RoHS Compliant (Note 1)
- "Green" Devices (Note 2)

Mechanical Data

- Case: SOT23-6
- Case material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.018 grams (approximate)

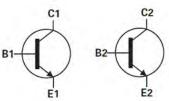
Applications

- LCD Backlighting inverter circuits
- Boost functions in DC-DC converters

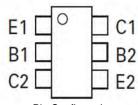
SOT-223



Top View



Device symbol



Pin Configuration

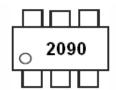
Ordering Information

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTD2090E6TA	2090	7	8	3000

Notes:

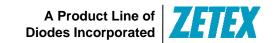
- 1. No purposefully added lead. Halogen and Antimony Free.
- 2. Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com.

Marking Information



2090 = Product type Marking Code





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Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	5	V
Continuous Collector Current (Note 5)	Ic	1	Α
Base current	I _B	200	mA
Peak Pulse Current	I _{CM}	2	Α

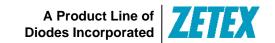
Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation at T _A = 25°C (Notes 3 & 6) Linear derating factor	P _D	0.90 7.2	W mW /°C
Power Dissipation at T _A = 25°C (Notes 3 & 7) Linear derating factor	P _D	1.1 8.8	W mW /°C
Power Dissipation at T _A = 25°C (Notes 4 & 6) Linear derating factor	P _D	1.7 13.6	W mW /°C
Thermal Resistance, Junction to Ambient (Notes 3 & 6)	$R_{ hetaJA}$	139	°C/W
Thermal Resistance, Junction to Ambient (Notes 4 & 6)	$R_{ heta JA}$	73	°C/W
Thermal Resistance, Junction to Ambient (Notes 3 & 7)	$R_{ heta JA}$	113	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 3. For a device surface mounted on 25mm X 25mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions
- 4. For a device surface mounted on FR4 PCB measured at < 5sec
- 5. Repetitive rating pulse width limited by maximum junction temperature. Refer to transient thermal impedance graph 6. For a device with one active die
- 7. For a device with two die running at equal power





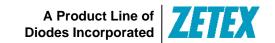
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Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	50			V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 8)	V _{(BR)CEO}	50			V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	I _E = 100μA
Collector-Base Cutoff Current	I _{CBO}			10	nA	V _{CB} = 40V
Collector-Emitter Cutoff Current	I _{CES}			10	nA	V _{CES} = 40V
Emitter Cutoff Current	I _{EBO}			10	. nA	$V_{EB} = 4V$
DC Current Gain (Note 8)	h _{FE}	200 300 200 75 20	420 450 350 130 60			$\begin{split} &I_{C} = 10\text{mA}, \ V_{CE} = 2\text{V} \\ &I_{C} = 100\text{mA}, \ V_{CE} = 2\text{V} \\ &I_{C} = 500\text{mA}, \ V_{CE} = 2\text{V} \\ &I_{C} = 1\text{A}, \ V_{CE} = 2\text{V} \\ &I_{C} = 1.5\text{A}, \ V_{CE} = 2\text{V} \end{split}$
Collector-Emitter Saturation Voltage (Note 8)	VCE(SAT)		24 60 120 160	35 80 200 270	mV mV mV	$I_C = 100$ mA, $I_B = 10$ mA $I_C = 250$ mA, $I_B = 10$ mA $I_C = 500$ mA, $I_B = 10$ mA $I_C = 1$ A, $I_B = 50$ mA
Base-Emitter Saturation Voltage (Note 8)	$V_{BE(sat)}$		940	1100	mV	$I_C = 1A, I_B = 50mA$
Base-Emitter Turn-On Voltage (Note 8)	V _{BE(ON)}		850	1100	mV	I _C = 1A, V _{CE} = 2V
Output Capacitance	C_obo		10		pF	V _{CB} = 10V. f = 1MHz
Current Gain-Bandwidth Product	f _T		215		MHz	V _{CE} = 10V, I _C = 50mA f = 100MHz
Turn-On Time	t _{on}		150		ns	V _{CC} = 10V, I _C = 1A
Turn-Off Time	t _{off}		425		ns	$I_{B1} = -I_{B2} = 100 \text{mA}$

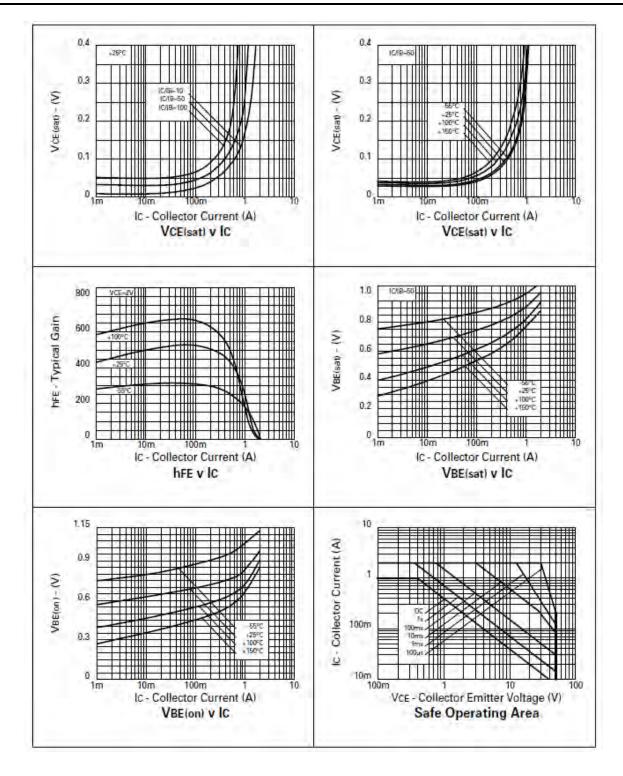
Notes: 8. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%





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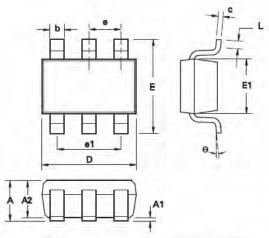
Typical Characteristics





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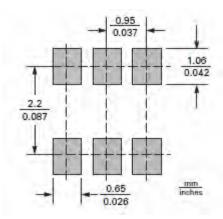
Package Outline Dimensions



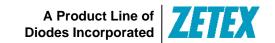
DIM	Millimeters		Inches			
	Min.	Max.	Min.	Max.		
Α	0.90	1.45	0.0354	0.0570		
A1	0.00	0.15	0.00	0.0059		
A2	0.90	1.30	0.0354	0.0511		
b	0.35	0.50	0.0078	0.0196 0.0102 0.1220		
C	0.09	0.26 3.10	0.0035 0.1062			
D	2.70					
E	2.20	3.20	0.0866	0.1181		
E1	1.30	1.80	0.0511	0.0708 0.0236		
L	0.10	0.60	0.0039			
е	0.95 REF		0.0374 REF			
e1	1.90	1.90 REF		0.0748 REF		
L	0°	30°	0°	30°		

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

Suggested Pad Layout







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